

BASIC ELECTRONICS

Soumitra Kumar Mandal



- ◆ Solved Examples- 500
- ◆ MCQs- 400
- ◆ Short questions with answers- 200
- ◆ Review Questions (numerical and theoretical)- 645
- ◆ Fill-in-the blanks- 170
- ◆ True and False type questions- 130
- ◆ Diagrams- 800



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Contents

Preface

xix

1. Introduction to Electronics and Semiconductors	1.1-1.88
1.1 Introduction	1.1
1.2 Signals	1.1
1.3 Frequency Spectrum of Signals	1.4
1.4 Analog, Discrete and Digital Signals	1.5
1.5 Amplifiers	1.6
1.6 Digital Logic Inverter	1.8
1.7 Semiconductors	1.9
1.8 Structure of Solids	1.11
1.9 Classification of Crystalline Structures	1.13
1.10 Density of a Crystal	1.16
1.11 Structure of the Atom	1.19
1.12 Energy-Level Diagram	1.26
1.13 Atomic Bonds	1.26
1.14 Energy-Band Theory	1.32
1.15 Energy Bands	1.35
1.16 Energy Bands in Crystals	1.36
1.17 Energy-Level Diagram of a Solid	1.38
1.18 Conductors, Semiconductors and Insulators	1.38
1.19 Conduction in Metals	1.40
1.20 Semiconductors	1.44
1.21 Donor Impurities	1.47
1.22 Acceptor Impurities	1.48
1.23 Conductivity of Intrinsic Semiconductors	1.49
1.24 Conductivity of <i>N</i> -type and <i>P</i> -type Semiconductors	1.51
1.25 Mass-Action Law	1.51
1.26 Charge Density in an <i>N</i> -type Semiconductor	1.52
1.27 Charge Density in a <i>P</i> -type Semiconductor	1.53
1.28 Electrical Properties of Semiconductor Materials (Ge and Si)	1.56
1.29 Hall Effect	1.59
1.30 Diffusion Current	1.62
1.31 Total Current	1.63
1.32 Einstein Relationship	1.63

1.33	Fermi-Dirac Function	1.64
1.34	Carrier Concentration in Intrinsic Semiconductor	1.66
1.35	Generation and Recombination	1.74
1.36	Continuity Equation	1.75
1.37	Minority Carrier Injected in a Semiconductor	1.78
	<i>Summary</i>	1.80
	<i>List of Important Formulae</i>	1.80
	<i>Short-Answer Questions</i>	1.82
	<i>Fill in The Blanks</i>	1.83
	<i>True/False Questions</i>	1.83
	<i>Multiple-Choice Questions</i>	1.83
	<i>Review Questions</i>	1.85
	<i>Answers</i>	1.88

2. PN-Junction Diodes

2.1-2.86

2.1	Introduction	2.1
2.2	Fabrication of a <i>PN</i> -Junction	2.1
2.3	Potential Variation within a Semiconductor	2.5
2.4	Open-Circuit Step-Graded <i>PN</i> -Junction	2.7
2.5	Open-Circuit <i>PN</i> -Junction	2.9
2.6	Formation of Depletion Layer in a <i>PN</i> -Junction	2.12
2.7	Unbiased <i>PN</i> -Junction	2.14
2.8	Biasing of a <i>PN</i> -Junction	2.15
2.9	Reverse Breakdown of <i>PN</i> -Junction	2.20
2.10	Energy-Band Structure of an Open-Circuit <i>PN</i> -Junction	2.20
2.11	Junction Capacitance	2.24
2.12	Depletion-layer Width, Electric Field and Depletion Layer Capacitance of <i>PN</i> -Junctions	2.26
2.13	Currents in a <i>PN</i> -Junction Diode	2.38
2.14	Circuit Symbol of a <i>PN</i> -Junction Diode	2.44
2.15	<i>V-I</i> Characteristic of a <i>PN</i> -Junction Diode	2.44
2.16	Determination of <i>V-I</i> Characteristics of a <i>PN</i> -Junction Diode	2.46
2.17	Effect of Temperature on <i>V-I</i> Characteristic Diode	2.49
2.18	Ideal Diode	2.50
2.19	Real Diode	2.51
2.20	Resistance of a <i>PN</i> -Junction Diode	2.52
2.21	Applications of <i>PN</i> -Junction Diode	2.54
2.22	Varactor Diodes	2.57
2.23	Tunnel Diode	2.58
2.24	Switching Times of a <i>PN</i> -Junction Diode	2.59
2.25	Specifications of <i>PN</i> -Junction Diodes	2.61
2.26	Optical Absorption	2.61
2.27	Photovoltaic/Solar Cells	2.65
2.28	Photodetectors	2.69
2.29	Pin Diode	2.73
2.30	Light-Emitting Diodes	2.74
2.31	Laser Diode	2.75
	<i>Summary</i>	2.77
	<i>List of Important Formulae</i>	2.78

<i>Short-Answer Questions</i>	2.79	
<i>Fill in the Blanks</i>	2.81	
<i>True/False Questions</i>	2.81	
<i>Multiple-Choice Questions</i>	2.82	
<i>Review Questions</i>	2.83	
<i>Answers</i>	2.86	
3. Rectifiers, Filters and Voltage Regulators		3.1–3.86
3.1	Introduction	3.1
3.2	Basic Diode Circuit	3.1
3.3	Piecewise Linear Model of a Diode	3.3
3.4	Clipping Circuits	3.10
3.5	Clamping Circuits	3.22
3.6	Voltage Multiplier	3.24
3.7	DC Power Supply	3.26
3.8	Rectifier	3.27
3.9	Single-Phase Full-Wave Rectifier	3.38
3.10	Single-Phase Bridge Rectifier	3.50
3.11	Comparison of Rectifiers	3.53
3.12	Filter	3.56
3.13	Zener Diode	3.61
3.14	Voltage Regulator	3.65
3.15	Zener Diode Shunt Regulator	3.66
3.16	Transistor Shunt Regulator	3.69
3.17	Transistor Series Regulator	3.69
	<i>Summary</i>	3.74
	<i>List of Important Formulae</i>	3.74
	<i>Short-Answer Questions</i>	3.76
	<i>Fill in The Blanks</i>	3.77
	<i>True/False Questions</i>	3.78
	<i>Multiple-Choice Questions</i>	3.78
	<i>Review Questions</i>	3.80
	<i>Answers</i>	3.86
4. Bipolar Junction Transistor		4.1–4.112
4.1	Introduction	4.1
4.2	Construction of Bipolar Junction Transistor	4.1
4.3	Formation of Bipolar Junction Transistors	4.2
4.4	Unbiased Bipolar Junction Transistor (BJT)	4.6
4.5	Biasing of Bipolar Junction Transistor (BJT)	4.7
4.6	Operating Mechanism of NPN Bipolar Junction Transistor	4.8
4.7	Operating Mechanism of PNP Bipolar Junction Transistor	4.9
4.8	Current in a Bipolar Junction Transistor	4.12
4.9	Circuit Configuration of a Bipolar Junction Transistor	4.12
4.10	Current Gain of a BJT in Common-Base Configuration	4.13
4.11	Current Gain of a BJT in Common-Emitter Configuration	4.14
4.12	Relation Between α and β	4.15
4.13	Current Gain of a BJT in Common-Collector Configuration	4.16
4.14	Leakage Current in Common-Base Configuration of BJT	4.17

4.15	Leakage Current in Common-Emitter Configuration of BJT	4.18
4.16	Energy-Band Diagram	4.21
4.17	Minority Carrier Concentration and Potential Barrier of a Transistor	4.23
4.18	Base Width Modulation or Early Effect	4.25
4.19	Current Components of a PNP Transistor	4.27
4.20	Transistor as Amplifier	4.28
4.22	Common-Emitter Configuration	4.34
4.23	Common-Collector Configuration of BJT	4.38
4.24	Comparison between CB, CE and CC Configurations of a BJT	4.39
4.25	Base-Spreading Resistance and Saturation Resistance	4.39
4.26	Specification of a Transistor	4.43
4.27	Model of Bipolar Junction Transistor	4.49
4.28	h -parameter Equivalent Circuit Model of BJT	4.51
4.29	Analysis of a Transistor Amplifier using h -parameters	4.54
4.30	Common-Emitter Amplifier	4.58
4.31	Common-Emitter Amplifier with Collector Feedback	4.60
4.32	Common-Base Amplifier	4.61
4.33	Common-Collector Amplifier	4.62
4.34	Comparison Between Common-Emitter, Common-Base and Common-Collector Amplifier	4.63
4.35	Conversion of h -parameters	4.63
4.36	Determination of h -parameters	4.64
4.37	Transistor as a Switch	4.68
4.38	Introduction to Transistor Biasing and Bias Stability	4.70
4.39	Operating Point and Load Line	4.70
4.40	Q-point and Output of Bipolar Junction Transistor	4.72
4.41	Stability Factor	4.73
4.42	Transistor Biasing	4.77
4.43	Fixed Bias	4.77
4.44	Voltage Divider or Self-Bias	4.82
4.45	Emitter Bias	4.84
4.46	Bias Compensation	4.96
4.47	Phototransistor	4.97
	Summary	4.98
	List of Important Formulae	4.99
	Short-Answer Questions	4.100
	Fill in the Blanks	4.101
	True/False Questions	4.101
	Multiple-Choice Questions	4.102
	Review Questions	4.105
	Answers	4.112

5.	Bipolar Junction Transistor Amplifiers: Small-Signal, Large-Signal, Multistage and Frequency Response	5.1–5.111
5.1	Introduction	5.1
5.2	Linear and Nonlinear Amplifiers	5.2
5.3	Classification of Amplifiers	5.3
5.4	Bipolar Junction Transistor (BJT) as a Linear Amplifier	5.3

5.5	Small-Signal Equivalent Circuit of Bipolar Junction Transistor	5.8
5.6	Common-Emitter Amplifier	5.14
5.7	Common-Base Amplifier	5.32
5.8	Common-Collector Amplifier	5.37
5.9	Comparison of Common-Emitter, Common-Base and Common-Collector Amplifiers	5.43
5.10	Cascode Amplifier	5.43
5.11	Darlington Connection of BJT	5.45
5.12	Introduction to Frequency Response of BJT Amplifiers	5.47
5.13	General Frequency Response of Amplifiers	5.47
5.14	Bode Plot of RC Circuit	5.49
5.15	Transient Response	5.52
5.16	High-Frequency and Low-Frequency Hybrid- π Model of a Bipolar Junction Transistor	5.53
5.17	Miller's Theorem	5.55
5.18	Dual of Miller's Theorem	5.56
5.19	Effect of Bypass Capacitor at Low-Frequency Response	5.56
5.20	Effect of Coupling Capacitance in Low-Frequency Response	5.58
5.21	Short-Circuit Current Gain in CE Amplifier	5.59
5.22	High-Frequency Current Gain with Resistive Load	5.60
5.23	Introduction to Multistage Amplifiers	5.61
5.24	Voltage Gain, Current Gain and Power Gain of Multistage Amplifiers	5.62
5.25	Coupling Schemes used in BJT Amplifiers	5.66
5.26	Analysis of Resistance Capacitance (RC) Coupled Amplifier	5.68
5.27	Impedance-Coupled Amplifier	5.77
5.28	Transformer Coupled Amplifier	5.78
5.29	Direct-Coupled Amplifier	5.82
5.30	Introduction to Large-Signal Amplifiers	5.85
5.31	Classification of Power Amplifiers	5.86
5.32	Class A Large-Signal Amplifier	5.87
5.33	Class A Transformer-Coupled Audio Power Amplifier	5.89
5.34	Efficiency of Class a Large-Signal Amplifier	5.90
5.35	Harmonic Distortion	5.92
5.36	Class B Large-Signal Amplifier	5.95
5.37	Class A Push-Pull Amplifier	5.97
5.38	Class B Push-Pull Amplifier	5.98
5.39	Crossover Distortion	5.99
5.40	Complementary Class B Push-Pull Amplifier	5.100
5.41	Class D Amplifier	5.101
	<i>Summary</i>	5.102
	<i>List of Important Formulae</i>	5.103
	<i>Short-Answer Questions</i>	5.105
	<i>Fill in the Blanks</i>	5.107
	<i>True/False Questions</i>	5.108
	<i>Multiple-Choice Questions</i>	5.108
	<i>Review Questions</i>	5.110
	<i>Answers</i>	5.111

6. Field Effect Transistor	6.1–6.59
6.1 Introduction	6.1
6.2 Classification of Field Effect Transistor	6.2
6.3 Junction Field Effect Transistor	6.2
6.4 Operation of JFET	6.6
6.5 Characteristics of JFET	6.9
6.6 Characteristic Parameters of JFET	6.14
6.7 Small-Signal Model of FET	6.15
6.8 Comparison Between FET and BJT	6.17
6.9 Comparison Between <i>N</i> -Channel FET and <i>P</i> -Channel FET	6.18
6.10 Applications of JFET	6.18
6.11 Metal Oxide Semiconductor Field Effect Transistor (MOSFET)	6.20
6.12 MOS Capacitor	6.20
6.13 <i>N</i> -Channel Enhancement MOSFET	6.22
6.14 <i>P</i> -Channel Enhancement MOSFET	6.27
6.15 <i>N</i> -Channel Depletion-Type MOSFET	6.29
6.16 <i>P</i> -Channel Depletion-Type MOSFET	6.30
6.17 Current-Voltage Relationship Between <i>N</i> -Channel MOSFET and <i>P</i> -Channel MOSFET	6.32
6.18 Comparison Between NMOS and PMOS	6.32
6.19 Circuit Symbols of JFET and MOSFET	6.32
6.20 Complementary MOSFET (CMOS)	6.33
6.21 Biasing of FET	6.34
6.22 FET Amplifier Configurations	6.40
<i>Summary</i>	6.49
<i>List of Important Formulae</i>	6.50
<i>Short-Answer Questions</i>	6.51
<i>Fill in The Blanks</i>	6.53
<i>True/False Questions</i>	6.53
<i>Multiple-Choice Questions</i>	6.54
<i>Review Questions</i>	6.56
<i>Answers</i>	6.59
7. Feedback Amplifier	7.1–7.46
7.1 Introduction	7.1
7.2 Feedback Amplifier	7.2
7.3 Classification of Amplifiers	7.6
7.4 Generalised Concept of Feedback Amplifiers	7.9
7.5 Topologies of Feedback Amplifiers	7.10
7.6 Effect of Feedback on Impedances	7.14
7.7 Properties of Feedback Amplifiers	7.22
7.8 Method of Analysis of a Feedback Amplifier	7.27
7.9 Practical Feedback Circuits	7.28
7.10 Stability of Feedback Amplifier	7.37
<i>Summary</i>	7.39
<i>List of Important Formulae</i>	7.40
<i>Short-Answer Questions</i>	7.41
<i>Fill in the Blanks</i>	7.41

<i>True/False Questions</i>	7.41	
<i>Multiple-Choice Questions</i>	7.42	
<i>Review Questions</i>	7.44	
<i>Answers</i>	7.46	
8. Oscillators		8.1–8.36
8.1 Introduction	8.1	
8.2 Classification of Oscillators	8.1	
8.3 The Basic Oscillator	8.3	
8.4 Oscillator Operation	8.4	
8.5 Phase Shift in Oscillation	8.6	
8.6 Phase Shift Oscillator	8.7	
8.7 BJT Phase-Shift Oscillator	8.8	
8.8 FET Phase-Shift Oscillator	8.11	
8.9 Wein-Bridge Oscillator	8.13	
8.10 Tuned Collector-Oscillator	8.16	
8.11 Tuned LC Oscillators	8.18	
8.12 Crystal Oscillators	8.28	
<i>Summary</i>	8.30	
<i>List of Important Formulae</i>	8.31	
<i>Short-Answer Questions</i>	8.31	
<i>Fill in The Blanks</i>	8.32	
<i>True/False Questions</i>	8.32	
<i>Multiple-Choice Questions</i>	8.33	
<i>Review Questions</i>	8.34	
<i>Answers</i>	8.36	
9. Operational Amplifier and Its Applications		9.1–9.91
9.1 Introduction	9.1	
9.2 The Ideal OP-AMP	9.3	
9.3 Equivalent Circuit of an OP-AMP	9.3	
9.4 Ideal Voltage Transfer Curve	9.4	
9.5 OP-AMP Symbol and Terminals	9.4	
9.6 The Package Style and Pin-outs	9.5	
9.7 Difference Amplifier	9.5	
9.8 Operational Amplifier Internal Circuit	9.10	
9.9 Open-Loop Configurations of OP-AMP	9.15	
9.10 Feedback in Ideal OP-AMP	9.16	
9.11 OP-AMP Characteristics	9.19	
9.12 Virtual Ground	9.28	
9.13 Frequency Response of Operational Amplifier	9.28	
9.14 Stability of Operational Amplifier	9.30	
9.15 Application of Operational Amplifier	9.31	
9.16 Inverting Amplifier	9.32	
9.17 Non-inverting Amplifier	9.33	
9.18 Voltage Follower	9.34	
9.19 Adder or Summing Amplifier	9.35	
9.20 Subtractor or Difference Amplifier	9.38	
9.21 Difference Amplifier with One OP-AMP	9.38	

9.22	Adder-Subtractor	9.39	
9.23	Voltage-to-Current Converter	9.44	
9.24	Current-to-Voltage Converter	9.45	
9.25	Integrator	9.45	
9.26	Differentiator	9.52	
9.27	Logarithmic Amplifier	9.55	
9.28	Antilog Amplifier	9.58	
9.29	Antilog Amplifier Using Transistor	9.59	
9.30	Analog Multiplier	9.59	
9.31	Analog Divider	9.61	
9.32	Comparator	9.63	
9.33	Schmitt Trigger	9.66	
9.34	Multivibrators	9.70	
9.35	Classification of Multivibrators	9.70	
9.36	Multivibrator Using OP-AMPS	9.71	
	Summary	9.80	
	List of Important Formulae	9.81	
	Short-Answer Questions	9.81	
	Fill in The Blanks	9.83	
	True/False Questions	9.83	
	Multiple-Choice Questions	9.84	
	Review Questions	9.86	
	Answers	9.91	
10.	Digital Circuits		10.1–10.120
10.1	Introduction	10.1	
10.2	Number Systems	10.2	
10.3	Binary Arithmetic	10.12	
10.4	Binary Coded Decimal (BCD) Number System	10.15	
10.5	Boolean Algebra	10.16	
10.6	Boolean Laws	10.18	
10.7	De Morgan's Theorem	10.22	
10.8	Logic Gates	10.24	
10.9	Universal Gate	10.27	
10.10	Digital Logic Circuits	10.30	
10.11	Combinational Logic	10.41	
10.12	Logic Simplification using Boolean Algebra	10.47	
10.13	Karnaugh Maps	10.51	
10.14	The Half-Adder	10.60	
10.15	The Full-Adder	10.61	
10.16	The 4-Bit Binary Full-Adder	10.63	
10.17	Half-Subtractor	10.65	
10.18	The Full-Subtractor	10.66	
10.19	Half-Adder/Subtractor	10.68	
10.20	2's Complement Adder/Subtractor	10.68	
10.21	Decoders	10.70	
10.22	Encoders	10.73	
10.23	Multiplexers	10.75	

- 10.24 Demultiplexer 10.79
 - 10.25 Introduction to Flip-Flops 10.81
 - 10.26 Memory Cell Using NAND and NOR Gates 10.82
 - 10.27 SR Latch Using NOR Gates 10.82
 - 10.28 SR Latch with Enable 10.83
 - 10.29 The *D* latch 10.84
 - 10.30 Edge-Triggered SR Flip-Flop 10.84
 - 10.31 Edge-Triggered *D* Flip-Flops 10.85
 - 10.32 T Flip-Flop 10.86
 - 10.33 JK Flip-Flop 10.88
 - 10.34 JK Master-Slave Flip-Flop 10.89
 - 10.35 Applications of Flip-Flops 10.90
 - 10.36 Register 10.91
 - 10.37 Shift-Register Counters 10.94
 - 10.38 Counter 10.96
 - 10.39 Asynchronous (Ripple) Counters 10.97
 - 10.40 Synchronous Counters 10.101
 - 10.41 Memory 10.105
 - 10.42 Classification of Memories 10.106
 - Summary 10.112
 - List of Important Formulae 10.112
 - Short-Answer Questions 10.113
 - Fill in the Blanks 10.114
 - True/False Questions 10.115
 - Multiple-Choice Questions 10.116
 - Review Questions 10.118
 - Answers 10.120
- 11. Electronic Instruments 11.1–11.57**
- 11.1 Introduction 11.1
 - 11.2 Digital Voltmeters 11.2
 - 11.3 Analog Multimeter 11.5
 - 11.4 Digital Multimeter 11.6
 - 11.5 $3\frac{1}{2}$ Digit Display of Digital Multimeter 11.10
 - 11.6 Auto-Range Digital Multimeters 11.10
 - 11.7 Resolution and Sensitivity of a Digital Multimeter 11.11
 - 11.8 Advantages of Digital Multimeters 11.12
 - 11.9 Comparison of Analog and Digital Multimeters 11.12
 - 11.10 Introduction to Cathode Ray Oscilloscope (CRO) 11.13
 - 11.11 Cathode Ray Tube 11.14
 - 11.12 Electrostatic Deflection of Electron Beam in a CRT 11.17
 - 11.13 Magnetic Deflection of Electron Beam in a CRT 11.19
 - 11.14 General-Purpose CRO 11.23
 - 11.15 Types of CRO 11.25
 - 11.16 Function of Sweep Generator 11.26
 - 11.17 General Appearance and Display System of a CRO 11.28
 - 11.18 Applications of CRO 11.31
 - 11.19 Lissajous Pattern 11.35

11.20	Digital Storage Oscilloscope (DSO)	11.38	
11.21	Introduction to Function Generator	11.40	
11.22	Fixed-Frequency Signal Generator	11.41	
11.23	Variable-Frequency Signal Generator	11.41	
11.24	Simplest Sine-Wave Signal Generator	11.41	
11.25	Standard Signal Generator	11.42	
11.26	Laboratory-Type Signal Generator	11.43	
11.27	Sine-Wave and Square-Wave Signal Generator	11.44	
11.28	Function Generator	11.45	
	<i>Summary</i>	11.48	
	<i>List of Important Formulae</i>	11.49	
	<i>Short-Answer Questions</i>	11.49	
	<i>Fill In the Blanks</i>	11.52	
	<i>True/False Questions</i>	11.52	
	<i>Multiple-Choice Questions</i>	11.52	
	<i>Review Questions</i>	11.54	
	<i>Answers</i>	11.57	
12.	Power Semiconductor Devices		12.1–12.51
12.1	Introduction	12.1	
12.2	Classification of Power Semiconductor Devices	12.2	
12.3	Power Diodes	12.3	
12.4	Schottky Power Diodes	12.8	
12.5	Fast-Recovery Power Diodes	12.9	
12.6	Thyristors	12.9	
12.7	Silicon Controlled Rectifier (SCR)	12.9	
12.8	Diode Model of Thyristor	12.12	
12.9	Two-Transistor Analogy of Thyristors	12.13	
12.10	Transient Model of a Thyristor	12.15	
12.11	Rating of Thyristor	12.15	
12.12	Turn-On or Triggering Methods of a Thyristor	12.16	
12.13	Single-Phase Controlled Rectifiers	12.18	
12.14	DIAC	12.29	
12.15	TRIAC	12.32	
12.16	Application of Triac in ac Voltage Controller	12.35	
12.17	Unijunction Transistor (UJT)	12.41	
	<i>Summary</i>	12.44	
	<i>List of Important Formulae</i>	12.45	
	<i>Short-Answer Questions</i>	12.46	
	<i>Fill in the Blanks</i>	12.47	
	<i>True/False Questions</i>	12.48	
	<i>Multiple-Choice Questions</i>	12.48	
	<i>Review Questions</i>	12.50	
	<i>Answers</i>	12.51	
13.	Transducers		13.1–13.34
13.1	Introduction	13.1	
13.2	Displacement-Measurement Transducers	13.3	
13.3	Strain Measurement	13.8	

- 13.4 Pressure Transducer 13.15
- 13.5 Piezoelectric Transducer 13.18
- 13.6 Temperature Transducer 13.19
- 13.7 Level Measurement 13.26
- 13.8 Flow Measurement 13.27

Summary 13.28

List of Important Formulae 13.30

Short-Answer Questions 13.30

Fill in the Blanks 13.31

True/False Questions 13.32

Multiple-Choice Questions 13.32

Review Questions 13.33

Answers 13.34

14. Communication Systems 14.1–14.47

14.1 Introduction 14.1

14.2 Elements of a Communication System 14.1

14.3 Operating Principles of Transmission and Reception 14.3

14.4 Modulation and Carrier Wave 14.3

14.5 Need for Modulation 14.4

14.6 Types of Analog Modulation 14.5

14.7 Amplitude Modulation (AM) 14.5

14.8 Block Diagram of an Amplitude-Modulation Transmitter 14.14

14.9 The Transistor Amplitude-Modulation (AM) Modulators 14.15

14.10 Square-Law Diode Modulation 14.17

14.11 Generation of Double Side Band Suppressed Carrier (DSB-SC) Signal 14.18

14.12 Generation of SSB-SC Signal 14.20

14.13 Frequency Modulation 14.22

14.14 Phase Modulation 14.25

14.15 Demodulation 14.27

14.16 Frequency-Modulation Detectors 14.30

14.17 Radio Transmission and Receiver 14.36

Summary 14.39

List of Important Formulae 14.39

Short-Answer Questions 14.40

Fill in the Blanks 14.42

True/False Questions 14.43

Multiple-Choice Questions 14.43

Review Questions 14.45

Answers 14.47

Additional Solved Problems ASP.1–ASP.47

Index I.1–I.9

Index

- α , 4.14
- β_0 , 4.15
- 2's Complement Adder/Subtractor, 10.68
- 3 dB cut-off frequencies, 5.47
- 3½ digit display of a multimeter, 11.10
- 4-bit binary full-adder, 10.63
- A**
- Absorption coefficient, 2.64
 - ac analysis, 5.20, 5.24, 5.26, 5.34, 5.39, 5.45
 - beta, 5.10
 - controller, 12.32
 - current gain, 4.14
 - load, 5.18
 - resistance, 5.12
 - voltage controller, 12.35
 - voltage controllers, 12.35
 - voltage regulators, 12.35
- Accelerating electrode, 11.15
- Accuracy, 11.1, 13.1
- Active region, 4.32, 4.36
- Active region, 5.3
- Active Transducers, 13.3
- Active, 4.7
- Adder-Subtractor, 9.39
- Alloy junction, 2.2
- Alloy type junctions, 4.3
- Ammeters, 11.1
- Amplification factor, 6.14, 6.15
- Amplifier, 1.6, 5.1
- Amplitude modulation, 14.5
- Amplitude multiplier, 11.45
- Amplitude, 1.2
- Analog
 - circuit, 5.2
 - instruments, 11.2
 - meters, 11.1
 - modulation, 14.5
 - multimeter, 11.12
 - signal, 1.5
 - transducers, 13.2
 - voltage divider, 9.61
 - voltage multiplier, 9.59
 - voltmeter, 11.2
- AND gate, 10.24
- AND operation, 10.18
- Anode to cathode, 12.32
- Antilog amplifier, 9.58, 9.59
- Antilog of a logarithmic, 9.58
- Astable multivibrator, 9.70, 9.73, 9.74
- Asynchronous (ripple) counters, 10.96
- Atomic mass, 1.19
- Atomic number, 1.19
- Atomic packing factor, 1.13
- Audio-frequency amplifier, 14.14
- Audio-frequency signal, 14.3
- Auto-range digital multimeter, 11.10
- Avalanche breakdown, 2.20, 4.44
- Azimuthal quantum number, 1.22
- B**
- Balanced modulator, 14.18
- Balanced slope detector, 14.31
- Bandwidth, 1.5
- Bandwidth, 5.48
- Barrier voltage, 2.13
- Base current, 4.8
- Base dc current gain, 4.14
- Base modulation, 14.15
- Base spreading resistance, 4.39
- Base transport factor, 4.11
- Base width modulation, 4.25
- Base, 4.1

- Baseband, 14.1, 14.3
 - Base-emitter input resistance, 5.8
 - Basic diode circuit, 3.1
 - Basic oscillator, 8.3
 - Beam finder, 11.29
 - Bellow, 13.17
 - Bias compensation, 4.96
 - Biased clamper, 3.24
 - Biased clipping, 3.13
 - Biasing of FET, 6.34
 - Biasing, 4.7
 - Bidirectional diode thyristor (DIAC), 12.1
 - Bidirectional shift registers, 10.93
 - Bidirectional triode thyristor (TRIAC), 12.1
 - bidirectional, 12.32
 - Binary addition, 10.12
 - Binary Coded Decimal (BCD), 10.15
 - Binary division, 10.13
 - Binary multiplication, 10.13
 - Binary number, 10.3
 - Binary subtraction, 10.13
 - Binary, 10.1
 - Binary-to-Decimal, 10.4
 - Binary-to-Hexadecimal, 10.10
 - Binary-to-Octal, 10.8
 - Bipolar device, 12.2
 - Bipolar junction transistor, 4.1
 - Bipolar logic families, 10.30
 - Bistable multivibrator, 9.70
 - BJT Phase Shift, 8.9
 - BJT, 4.1
 - Blocking capacitors, 5.14
 - Bode Plot, 5.49
 - Bode plots, 5.47
 - Body Centered Cubic, 1.13
 - Bohr atom model, 1.24
 - Bond energy, 1.27
 - Bond length, 1.27
 - Bonded strain gauges, 13.9
 - Boolean algebra, 10.16
 - Boolean laws, 10.18
 - Bourdon tube, 13.15
 - Breakdown diode, 3.61
 - Breakdown voltage, 2.48
 - Break region, 3.6
 - Breakdown region, 12.5, 6.12
 - Breakdown voltage, 2.20, 6.12
 - Breakover current, 3.63
 - Break-over voltage, 12.29, 12.31
 - Bridge rectifier, 3.50, 12.27
 - Buffer amplifier, 14.14
 - Buffer, 9.10
- ## C
- Calendar equation, 13.20
 - Capacitive-displacement transducer, 13.5
 - Capacitor filter, 3.57
 - Carrier swing, 14.24
 - Carrier wave, 14.3
 - Cascade demultiplexer, 10.80
 - Cascading decoders, 10.73
 - Cascode amplifier, 5.43
 - Cathode ray oscilloscope, 11.13
 - Cathode Ray Tube (CRT), 11.14, 11.24
 - Center-tapped, 3.39
 - Centre frequency, 14.24
 - Channel, 14.2
 - Characteristics of OP-AMPS, 9.3
 - Charge sensitivity, 13.19
 - Clamping, 3.10
 - Class A Gain Stage, 9.11
 - Clipping, 3.10
 - Closed-loop gain, 9.30
 - Collector current, 4.8
 - Collector cut-off current, 4.18
 - Collector Modulation, 14.16
 - Collector to emitter leakage current, 4.19
 - Collector, 4.2
 - Colpitts oscillator, 8.19, 8.20
 - Combination clipper, 3.18
 - Common base amplifier, 4.61, 5.32
 - Common base configuration, 4.12
 - Common collector amplifier, 4.62, 5.37
 - Common collector configuration, 4.12
 - Common emitter amplifier, 4.58, 5.14
 - Common emitter configuration, 4.12
 - Common-drain (CD) amplifier, 6.40
 - Common-Drain, 6.42
 - Common-gate (CG) amplifier, 6.40
 - Common-Gate (CG), 6.44
 - Common-mode rejection ratio (CMRR), 9.7, 9.23
 - Common-source (CS) amplifier, 6.40
 - Communication equipments, 14.1
 - Communication system, 14.1
 - Communication, 14.1
 - Commutation, 12.19
 - Comparator, 3.20, 9.63
 - Complementary MOSFET (CMOS), 6.33
 - Conduction band, 1.34

- Conductivity, 1.42, 1.49, 1.58
- Conductor, 1.38
- Contact difference of potential, 2.7
- Contact-Bounce Elimination, 10.90
- Continuity equation, 1.75
- Conversion CE to CB, 4.63
- Conversion CE to CC, 4.64
- Count-Down Counter, 10.97
- Counter, 10.96
- Count-Up Counter, 10.97
- Coupling capacitors, 5.14
- Covalent bond, 1.30
- Crystal Oscillators, 8.28
- Crystal structure, 1.11
- Crystalline, 1.11
- Current density, 1.41
- Current gain, 4.29, 4.55
- Current hogging, 10.35
- Current limiting resistance, 3.68
- Current measurement, 11.35
- Cut-off frequency, 5.47
- Cut-off region, 4.33, 4.36
- Cut-off voltage, 6.7
- Cut-off, 4.7
- Czochralski, 2.1
- D**
- D flip-flop, 10.85
- D latch, 10.84
- Darlington, 5.45
- dc analysis, 5.20, 5.24, 5.34, 5.39, 5.45
- dc beta, 5.10
- dc power supply, 3.26
- DCTL, 10.35
- De Morgan's theorem, 10.22
- Dead band, 9.73
- Decade counters, 10.100
- Decimal Number, 10.2
- Decimal-to-Binary, 10.4
- Decimal-to-Hexadecimal, 10.10
- Decimal-to-Octal Conversion, 10.7
- Decoders, 10.70
- Deflection factor, 11.19
- Delay line, 11.24
- Delay time, 4.69
- Demodulation, 14.27
- Demultiplexer, 10.80
- Density of a crystal, 1.16
- Depletion layer capacitance, 2.24
- Depletion layer., 2.13
- Depletion MOSFET, 6.29
- Depletion region, 2.9
- Depletion region-capacitance, 2.24
- Depletion, 6.4, 6.29
- Depletion-type MOSFET, 6.30
- DIAC, 12.29
- Diaphragm, 13.16
- Difference amplifier, 9.5
- Differential amplifier, 9.11, 9.12, 9.15, 9.38
- Differentiator, 9.52
- Diffused junction, 2.3
- Diffusion capacitance, 2.25
- Diffusion current, 1.62, 1.79, 4.27
- Diffusion of electrons, 2.13
- Diffusion of holes, 2.13
- Diffusion resistance, 5.8
- Diffusion type junction, 4.4
- Digital ICs, 9.2
- Digital instruments, 11.2
- Digital Logic Circuits, 10.30
- Digital Multimeter, 11.6, 11.8, 11.12
- Digital signal, 1.5
- Digital Storage Oscilloscope (DSO), 11.25, 11.38, 11.40
- Digital thermometer, 13.25
- Digital transducers, 13.2
- Digital voltmeters, 11.2
- Digital Volt-Ohm-Milli-ammeter (DVOM), 11.8
- Diode circuit with dc source, 3.8
- Diode compensation, 4.96
- Diode model of thyristor, 12.12
- Diode voltage, 3.29
- Discrete circuit, 9.1
- Discrete-time signal, 1.5
- Displacement, 13.3
- Divide-by-8 counter, 10.97
- Divider, 9.61
- Donor or N-type impurities., 1.47
- Donors, 1.47
- Double complement, 10.20
- Drain Characteristics, 6.10
- Drain resistance, 6.14, 6.15
- Drain, 6.4
- Drift current, 1.63, 1.79
- Drift region, 12.3, 12.4
- Drift velocity, 1.40
- DSB-SC, 14.11
- DSO, 11.40
- DTL, 10.36
- Dual-slope integrating-type DVM, 11.2

Dual-trace Controls, 11.30
 Dynamic characteristics, 3.2
 Dynamic RAMs, 10.108
 Dynamic resistance, 2.53

E

Early effect, 4.25
 Ebers-moll model, 4.49
 ECL, 10.37
 Edge-Triggered, 10.84
 EEPROM, 10.107
 Efficiency, 3.33, 3.45
 Einstein equation, 1.64
 Einstein Relationship, 1.63
 Electric field, 2.10
 Electrical transducer, 13.1
 Electromagnetic flowmeter, 13.27
 Electron inversion layer, 6.21
 Electron lens, 11.15
 Electron orbits, 1.19
 Electron, 1.47
 Electrostatic deflection, 11.17
 Emitter bias, 4.84
 Emitter current, 4.8
 Emitter Modulation, 14.15
 Emitter, 4.1
 Encoders, 10.73
 Energy-band diagrams of BJT, 4.21
 Energy-gap, 1.58
 Energy-level diagram, 1.26
 Enhancement mode states, 6.22
 Enhancement, 6.23
 Envelope detector, 14.29
 Epitaxial growth junction, , , , 2.4
 Epitaxial type junctions, 4.5
 EPROM, 10.107
 Error, 11.2
 Exclusive-NOR gate, 10.26
 Exclusive-OR gate, 10.26
 Extrinsic or impure semiconductor, 1.44

F

Face centred cubic, 1.15
 Fall time, 4.70
 Fan-in, 10.33
 Fan-out, 10.33
 Fast-recovery diode, 12.7, 12.9
 Fast-recovery Power, 12.9
 Feedback Oscillators, 8.2
 Fermi-Dirac distribution function, 1.64
 Fermi level, 1.64

FET Amplifier, 6.40
 FET Phase-Shift, 8.11
 Filter, 3.56
 π -filter, 3.60
 First-stage differential amplifier, 9.10
 Fixed bias with collector feedback, 4.80
 Fixed bias with emitter feedback, 4.77
 Fixed bias, 4.77
 Fixed-frequency signal generator, 11.41
 Floating zone technique, 2.1
 Flow measurement, 13.27
 Fluorescent screen, 11.16
 Focus control, 11.29
 Focusing anode, 11.15
 Forced commutation, 12.18
 Forward bias, 2.15
 Forward blocking, 12.10
 Forward characteristic, 2.46
 Forward conduction, 12.10
 Forward recovery time, 2.59
 Forward-blocking region, 12.11
 Forward-conduction region, 12.12
 Foster-Seeley discriminator, 14.34
 Fourier transform, 1.4
 Fractional decimal number, 10.5
 Frequency division, 10.90
 Frequency measurement, 11.37
 Frequency modulation (FM), 14.5, 14.22
 Frequency multiplier, 11.45
 Frequency ratio, 11.37
 Frequency response of BJT, 5.47
 Frequency selector, 11.45
 Frequency spectrum, 1.4
 Frequency, 1.2
 Frequency-discrimination, 14.21
 Frequency-modulation receiver, 14.38
 Friction error, 11.6
 Full-adder, 10.61
 Full-subtractor, 10.66
 Function generator, 11.40, 11.45

G

Gate bias, 6.34
 Gate current (IG), 12.15
 Gate triggering, 12.17
 Gate, 6.4
 Gauge factor, 13.11, 13.12
 Graded semiconductor, 2.5
 Graticule, 11.28, 11.29
 Grounded collector amplifier, 5.37
 Grown junction, 2.1

Grown type junctions, 4.3

H

Half-adder, 10.60
 Half-adder/subtractor, 10.68
 Half-subtractor, 10.65
 Half-wave semi-converter, 12.20
 Hall effect, 1.59
 Hartley oscillator, 8.19, 8.23
 Heat sink, 4.47
 Hexadecimal number, 10.9
 Hexadecimal-to-binary, 10.10
 High sensitivity, 13.7
 higher cut-off frequency, 5.47
 High-frequency model of FET, 6.16
 Holding Current (IH), 12.15
 Hole inversion layer, 6.22
 Hole, 1.48
 Horizontal Position Control, 11.30
 Horizontal Sensitivity Control, 11.30
h-parameter model, 4.49, 5.26
h-parameter, 5.34, 5.39
 Hybrid ICs, 9.1
 Hybrid-*p* model, 5.8
 Hybrid-*p*, 5.27
 Hysteresis, 9.72

I

Ideal diode, 2.50
 Ideal OP-AMP, 9.3
 Ideal voltage transfer curve, 9.4
 Ideal zener diode, 3.63
 I-layer, 12.4
 Inductor filter, 3.57
 Inductor-capacitor filter, 3.59
 Injected current, 4.8
 Injection efficiency, 4.11
 Input bias current, 9.21
 Input characteristics, 4.31
 Input offset current (I_{IOS}), 9.21
 Input offset voltage, 9.21
 Input resistance, 4.55, 4.59, 6.41, 6.43, 6.45
 Input Transducers, 13.2, 14.2
 Insulated gate field effect transistor, 6.2
 Insulator, 1.39
 Integrated circuit (IC), 9.1
 Intensity control, 11.29
 Intrinsic concentration, 1.57
 Intrinsic or pure semiconductor, 1.44
 Inversion operation, 10.17

Inverter, 1.8
 Inverting amplifier, 9.15, 9.32
 Inverting comparator, 9.64
 Inverting summing amplifier, 9.35
 Inverting, 9.32
 Ionic bond, 1.27

J

JK flip-flop, 10.88
JK master-slave flip-flop, 10.89
 Johnson counters, 10.95
 Junction capacitance, 2.24
 Junction field effect transistor, 6.2
 Junction voltage, 2.13

K

Karnaugh maps, 10.51
 Kilovoltmeter, 11.5
 Knee point, 4.31

L

LASER diode, 2.75
 Latching current (I_L), 12.15
 Latching current, 12.15
 Lattice, 1.11
 LC oscillators, 8.2
 LED, 2.74
 Left-Shift Registers, 10.92
 Level measurement, 13.26
 Level shifter, 9.10
 Light spectrum, 2.66
 Light triggering, 12.17
 Light-emitting diode, 2.74
 Limiting, 3.10
 Line commutation, 12.19
 Line regulation, 3.65
 Linear (analog) ICs, 9.2
 Linear amplifier, 1.6, 5.2, 5.3, 5.5
 Linear Diode Detector, 14.29
 Linear Region, 6.10
 Linear Variable Differential Transformer, 13.6
 Linear, 6.7
 Linearity, 13.1, 13.7
 Linearly graded junction, 2.30
 Lissajous pattern, 11.13, 11.35, 11.36
 Load line, 3.1
 Load regulation, 3.66
 Log and antilog amplifiers, 9.55
 Logarithmic amplifier, 9.57
 Logic Gates, 10.24

Logic Simplification, 10.55
 Lower cut-off frequency, 5.47
 Lower Side-Band (LSB), 14.8
 Lower threshold voltage, 9.67
 Low-Frequency Model of FET, 6.16
 LSI, 9.2

M

Magnetic deflection, 11.19, 11.20
 Magnetic flowmeter, 13.27
 Magnetic quantum number, 1.22
 Majority carrier current, 2.14, 2.41
 Majority carrier, 12.2
 Mass-action law, 1.51
 Maximum collector current, 4.43
 Maximum output voltage, 4.44
 Maximum power dissipation, 3.63, 4.44
 Memory operation, 10.109
 Memory organisation, 10.108
 Memory, 10.82, 10.105
 Metallic bond, 1.32
 Metal-Oxide-Semiconductor, 6.1
 Miller's Theorem, 5.55
 Milli-ammeter, 11.5
 Millivoltmeter, 11.5
 Minority carrier concentration, 4.23
 Minority carrier current, 2.15, 2.41
 Minority carrier, 12.2
 Mobility, 1.57
 Modulated wave, 14.4
 Modulation Index (m), 14.8, 14.25
 Modulation, 14.4
 Monolithic ICs, 9.1
 Monostable multivibrator, 9.70
 MOS Capacitor, 6.20
 MSI, 9.2
 Multiplier circuit, 9.60
 Multivibrators, 9.70

N

NAND gate, 10.26
 Natural commutation, 12.18
N-Channel Depletion Type MOSFET, 6.29
N-channel enhancement, 6.26
N-channel JFET, 6.4
 Negative clamper, 3.23
 Negative clipping, 3.12
 Noise immunity, 10.33
 Noise, 14.2
 Non-inverting amplifier, 9.16, 9.33
 Non-inverting comparator, 9.63

Non-inverting summing amplifier, 9.35
 Nonlinear amplifier, 1.6, 5.2
 Nonperiodic, 1.2
 Nonsaturation region, 6.27
 Nonsinusoidal oscillators, 8.2
 NOR Gate, 10.25
n-p-n transistor, 4.1
 Number systems, 10.2
 Nyquist plot, 8.5

O

Octal number, 10.7
 Offset voltage adjustment, 9.22
 Ohm-meter, 11.1, 11.5
 One sided abrupt junction, 2.29
 One-bit memory element, 10.81
 OP-AMP characteristics, 9.19
 OP-AMPs as Bistable, 9.71
 Operating point, 4.70
 Operational amplifier, 9.2
 OR gate, 10.25
 OR operation, 10.17
 Oscillator operation, 8.4
 Oscillator, 8.1
 Oscillogram, 11.26
 Output characteristic, 4.32
 Output resistance, 4.56, 4.59, 6.42, 6.43, 6.45
 Output stage, 9.12
 Output transducers, 13.2, 14.3
 Overmodulation, 14.9

P

Parallax error, 11.5
 Passive transducers, 13.2
 Pauli's exclusion principle, 1.23, 1.33
P-channel enhancement, 6.27
 Peak Inverse Voltage (PIV), 3.29, 3.42
 Percentage modulation, 14.8
 Periodic, 1.2
 Phase discriminator, 14.33
 Phase measurement, 11.33, 11.36
 Phase Modulation (PM), 14.5, 14.25
 Phase shift in oscillation, 8.6
 Phase shift oscillator, 8.7
 Phase, 1.3
 Phase-Controlled, 12.35
 Phase-Shift Method, 14.21
 Photoconductor, 2.69
 Photodetectors, 2.69
 Photodiode, 2.70

- Photon absorption, 2.62
 - Photon flux, 2.64
 - Phototransistor, 4.97
 - Photovoltaic cell, 2.65
 - Piecewise linear model, 3.3
 - Piezoelectric transducer, 13.18
 - p-i-n diode, 12.4
 - PIN diode, 2.73
 - Pinch-off voltage, 6.8
 - Platinum Resistance Thermometer (PRT), 13.21
 - PN*-junction diode, 2.44, 12.9
 - PN*-junction, 2.20
 - P-N-P* transistor, 4.1
 - Point contact junction, 2.5
 - Poisson's equation, 2.10
 - Polycrystalline, 1.11
 - Poor accuracy, 11.6
 - POS, 10.45
 - Positive clamper, 3.23
 - Positive clipping, 3.10
 - Potential barrier, 2.12
 - Potential energy, 1.36
 - Potentiometer, 13.3
 - Power amplifier, 14.14
 - Power diodes, 12.3
 - Power dissipation, 10.32
 - Power gain, 4.29, 4.57
 - Power supply, 11.24
 - Practical difference amplifier, 9.6
 - Practical differentiator, 9.52
 - Precision, 11.1
 - Pressure Transducer, 13.15
 - Principle quantum number, 1.22
 - PROM, 10.107
 - Propagation delay, 10.31
 - P-type or acceptor impurities, 1.48
 - Pulse generator, 9.76
 - Punch through, 4.25, 4.44
- Q**
- Q-point, 4.70
 - Quantum mechanics, 1.20
 - Quiescent (Q) operating, 5.4
 - Quiescent base current, 5.5
 - Quiescent point, 4.70
- R**
- Radio receiver, 14.37
 - Radio transmitter, 14.36
 - Radio-frequency, 14.3
 - Radix, 10.2
 - Range, 13.1
 - r_e model, 5.12, 5.22, 5.28
 - r_e parameter, 5.35, 5.41
 - Real diode, 2.51
 - Real zener diode, 3.63
 - Receiver, 14.3
 - Recombination rate, 1.74
 - Rectifier, 3.27
 - Regenerative comparator, 9.67
 - Register, 10.91
 - Relaxation oscillator, 12.43
 - Resistance Thermometer, 13.19
 - Resistivity, 1.42
 - Resolution, 11.2, 13.1, 13.7
 - Retrace time, 11.26
 - Return time, 11.26
 - Reverse bias, 2.15
 - Reverse blocking states, 12.10
 - Reverse breakdown voltage VBD, 12.5
 - Reverse characteristic, 2.48
 - Reverse recover time, 2.59
 - Reverse recovery charge, 12.7
 - Reverse recovery time, 12.5
 - Reverse saturation current, 2.19, 2.40, 2.46, 4.8, 4.18
 - Reverse-blocking region, 12.12
 - Right shift registers, 10.93
 - Ring counters, 10.94
 - Ring modulator, 14.19
 - Ripple factor, 3.31, 3.44
 - Rise time t_r , 4.69, 5.53
 - ROM, 10.107
 - RTL, 10.35
- S**
- Saturation (Pinch-off) Region, 6.10
 - Saturation region, 4.33, 4.37, 6.9
 - Saturation resistance, 4.39
 - Saturation, 4.7
 - Scale changer, 9.32
 - Scale Error, 11.5
 - Schmitt trigger circuit, 9.67
 - Schmitt trigger, 9.66, 9.72
 - Schrodinger's equation, 1.1
 - Schottky diodes, 12.9
 - Schottky power diodes, 12.8
 - Schottky TTL, 10.38
 - SCR, 12.9

- Second-stage differential amplifier, 9.10
 - Self-bias, 6.35
 - Self-decoding, 10.94
 - Self-generating transducers, 13.3
 - Semiconductor, 1.9, 1.39
 - Sensistor bias compensation, 4.97
 - Sensitivity, 11.1, 11.31, 13.1
 - Series positive clipper, 3.11
 - Series regulator, 3.69
 - Shift Register, 10.91
 - Shockley's equation, 6.11
 - Shunt negative clipper, 3.12
 - Shunt regulator, 3.66
 - Sign changer, 9.32
 - Signal generator, 11.43
 - Signals, 1.1
 - Silicon-controlled rectifier (SCR), 12.1
 - Sine-wave signal generator, 11.41
 - Sine-wave to square-wave converter, 9.66
 - Sine-wave, 11.44
 - Single phase full wave rectifier, 3.38
 - Single phase half wave rectifier, 3.27
 - Single-phase ac voltage controller, 12.39
 - Single-phase full-wave Controlled, 12.24
 - Single-Phase half-controlled, 12.19
 - Single-phase half-wave, 12.37
 - Single-phase, 12.37
 - Sinusoidal oscillators, 8.1
 - Slew Rate (SR), 9.24
 - Slope Detector, 14.31
 - Small-signal amplifier, 4.70
 - Small-signal analysis, 5.47
 - Soft-recovery diode, 12.7
 - SOP, 10.42
 - Source, 6.3
 - Space charge capacitance, 2.24
 - Space charge region, 2.10
 - Specifications of digital multimeters, 11.9
 - Specifications of LVDTs, 13.8
 - Specifications of RTDs, 13.22
 - Specifications of strain gauge, 13.14
 - Specifications, 11.40
 - Spin quantum number, 1.23
 - Square-law detectors, 14.28
 - Square-law diode modulation, 14.17
 - Square-wave, 11.44
 - SR latch with enable, 10.83
 - SR latch, 10.82
 - SSB-SC, 14.11
 - SSB-TC, 14.11
 - SSI, 9.2
 - Stability factor, 4.73
 - Stability, 9.30
 - Staircase ramp-type digital voltmeter, 11.4
 - Standard signal generator, 11.42
 - Static characteristics, 3.2
 - Static RAMs, 10.108
 - Static resistance, 2.52
 - Step graded *PN*-junction, 2.26
 - Step grading, 2.7
 - Step-graded junction, 2.1, 2.7
 - Storage capacitance, 2.25
 - Storage time, 4.69
 - Strain gauge, 13.9
 - Strain measurement, 13.8
 - Strain transducer, 13.9
 - Sub-shells, 1.20
 - Subtractor, 9.38
 - Summing amplifier, 9.35
 - Summing differentiator, 9.53
 - Summing integrator, 9.48
 - Superheterodyne receiver, 14.37
 - Supply voltage rejection ratio (SVRR), 9.23
 - Swamped amplifier, 5.30
 - Sweep generator, 11.26
 - Sweep time, 11.26
 - Sweep-voltage frequency, 11.27
 - Symbols
 - Synchronous Counters, 10.97, 10.101
 - Synchronous Decade Counters, 10.104
- T**
- T* flip-flop, 10.86, 10.87
 - T* Latch, 10.86
 - Transistor biasing, 4.77
 - Temperature Transducer, 13.19
 - Tetrahedral, 1.16
 - Thermal runaway, 4.46
 - Thermal triggering, 12.17
 - Thermal voltage drift, 9.22
 - Thermistor Compensation, 4.96
 - Thermistor, 13.22
 - Threshold voltage, 4.31
 - Time Base or Sweep Generator, 11.24
 - Time constant t , 5.52, 13.23
 - Time Period and Frequency Measurement, 11.32
 - Time-Base Controls, 11.29
 - Total current density, 1.1
 - Total modulation index, 14.10

Trace time, 11.26
 Transconductance, 5.9, 6.14, 6.15
 Transducer, 13.1
 Transfer Characteristics of Differential Amplifier, 9.13
 Transfer characteristics, 3.2, 6.10, 6.13
 Transformer Utilization Factor (TUF), 3.36
 Transient Response, 5.52
 Transistor as a switch, 4.68
 Transistor as an amplifier, 4.28
 Transistor series regulator, 3.69
 Transistor shunt regulator, 3.69
 Transition region capacitance, 2.24
 Transition region, 2.10
 Transition time, 2.60
 Transmitter, 14.2
 TRIAC, 12.32
 Triangular waveform generator, 9.78
 Triangular waveform, 9.78
 Trigger circuit, 11.24
 Triggering methods, 12.16
 Triggering, 12.2
 Triode ac switch, 12.32
 TTL, 10.36
 Tuned collector-oscillator, 8.16
 Tuned LC oscillators, 8.18
 Tunnel diode, 2.58
 Turn-off time, 4.70
 Turn-on time, 4.69
 Turn-on characteristics, 12.17
 Turn-on, 12.16
 Twisted ring counters, 10.95
 Two-terminal ac switch, 12.31
 Two-Transistor Analogy of Thyristors, 12.13

U

UJT, 12.41
 ULSI, 9.2
 UNBIASED BJT, 4.6
 Unbiased junction, 2.14
 Unbonded gauges, 13.9
 Uncovered charges, 2.10
 Unidirectional Shift Registers, 10.92
 Unidirectional voltage controller, 12.37
 Unidirectional, 12.32
 Unijunction transistor (UJT), 12.1, 12.41
 Unipolar device, 12.2
 Unit cell, 1.12
 Universal Gate, 10.27
 Upper Side-Band (USB), 14.8

Upper threshold voltage, 9.67

V

Valence band, 1.34
 Valence electrons, 1.23
 Varactor diode, 2.57
 Variable parameter transducers, 13.2
 Variable-frequency signal generator, 11.41
 Vertical amplifier, 11.24
 Vertical position control, 11.30
 Vertical sensitivity and polarity controls, 11.29
 Vestigial Side Band (VSB), 14.12
 V-I Characteristic, 2.44
 Virtual ground, 9.28, 9.58
 VLSI, 9.2
 Voltage amplifier factor, 4.28
 Voltage divider or self bias, 4.82
 Voltage Doubler, 3.24
 Voltage follower, 9.34
 Voltage gain, 4.29, 4.56, 4.59, 6.41, 6.43, 6.44
 Voltage measurement, 11.31
 Voltage multiplier, 3.24
 Voltage quadrupler, 3.25
 Voltage regulation, 3.32
 Voltage regulator diode, 3.61
 Voltage regulator, 3.65
 Voltage Safety Factor (VSF), 12.16
 Voltage tripler, 3.25
 Voltage-controlled device, 6.1
 Voltage-Divider Bias, 6.37
 Voltage-Level Shifter, 9.12
 Voltage-to-current converters, 9.44
 Voltmeter, 11.1, 11.5
 Volt-Ohm-Milli-ammeter (VOM), 11.5

W

Wavelength, 1.3
 Wein-bridge oscillator, 8.13, 11.44
 Wheatstone bridge, 13.12

Z

Zener breakdown voltage, 3.63
 Zener breakdown, 2.20, 3.61
 Zener diode shunt regulator, 3.66
 Zener diode, 3.61
 Zener resistance, 3.63
 Zero Error, 11.5
 Zero-crossing detector, 9.66